## **HSB83**

Silicon Epitaxial Planar Diode for High Voltage Switching

# **HITACHI**

ADE-208-489A(Z) Rev 1 Nov. 1999

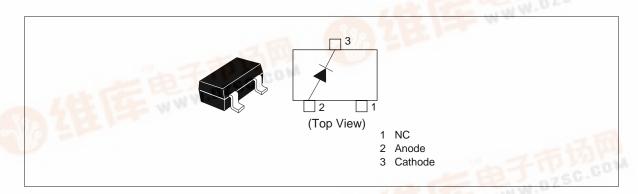
#### **Features**

- High reverse voltage. (VR=250V)
- CMPAK package is suitable for high density surface mounting and high speed assembly.

#### **Ordering Information**

Type No.	Laser Mark	Package Code
HSB83	F7	CMPAK

#### **Outline**





## HSB83

## Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	300	V
Reverse voltage	$V_R$	250	V
Peak forward current	I <sub>FM</sub>	300	mA
Non-Repetitive peak forward surge current	I <sub>FSM</sub> <sup>*1</sup>	2	A
Average rectified current	Io	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: 1. Value at duration of 10msec.

#### Electrical Characteristics ( $Ta = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F</sub>	_	_	1.2	V	I <sub>F</sub> = 100 mA
Reverse current	I <sub>R1</sub>	_	_	0.2	μΑ	V <sub>R</sub> = 250V
	I <sub>R2</sub>	_	_	100		V <sub>R</sub> = 300V
Capacitance	С	_	_	3.0	pF	$V_R = 0V, f = 1 MHz$
Reverse recovery time	t <sub>rr</sub>	_	_	100	ns	$I_F = I_R = 30 \text{ mA}, I_{rr} = 3\text{mA}, R_L = 100\Omega$

#### **Main Characteristic**

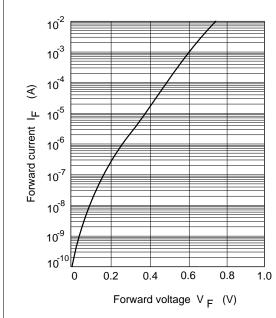


Fig.1 Forward current Vs. Forward voltage

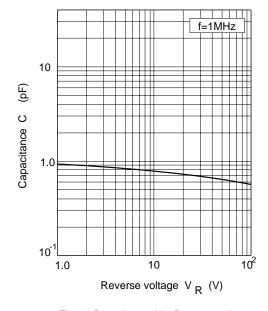


Fig.3 Capacitance Vs. Reverse voltage

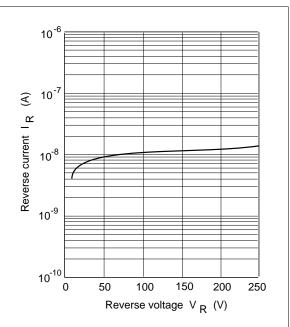
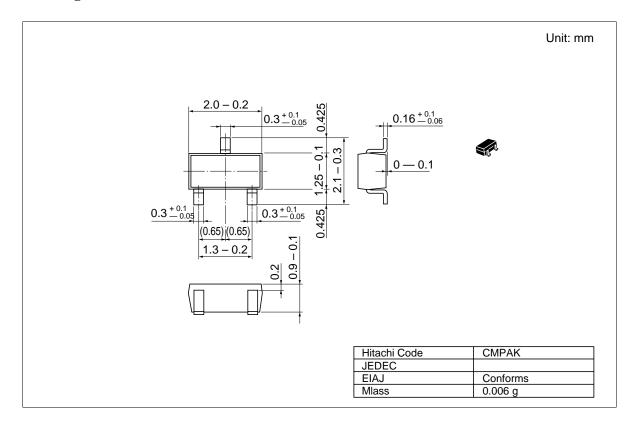


Fig.2 Reverse current Vs. Reverse voltage

## **HSB83**

## **Package Dimensions**



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